

MOSFETs Silicon N-Channel MOS (DTMOSVI)

TK190A60Z1

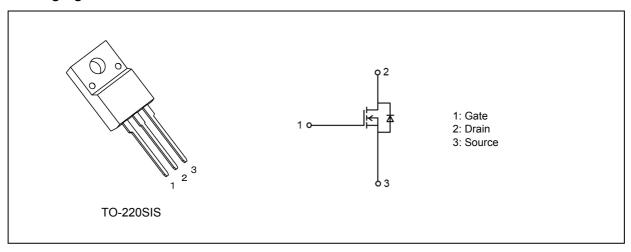
1. Applications

· Switching Power Supplies

2. Features

- (1) Low drain-source on-resistance: $R_{DS(ON)} = 0.158 \Omega$ (typ.)
- (2) High-speed switching properties with the lower capacitance.
- (3) Enhancement mode: $V_{th} = 3$ to 4 V ($V_{DS} = 10$ V, $I_D = 0.48$ mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Rating | Unit | | |
|--------------------------------|--------------------------|----------|-----------------------|------------|-------|
| Drain-source voltage | | | V _{DSS} | 600 | V |
| Gate-source voltage | | | V _{GSS} | ±30 |] |
| Drain current (DC) | | (Note 1) | I _D | 14 | Α |
| Drain current (pulsed) | | (Note 1) | I _{DP} | 56 |] |
| Power dissipation | (T _c = 25 °C) | | P _D | 40 | W |
| Single-pulse avalanche energy | | (Note 2) | E _{AS} | 127 | mJ |
| Single-pulse avalanche current | - | | I _{AS} | 3.3 | Α |
| Reverse drain current (DC) | | (Note 1) | I _{DR} | 14 |] |
| Reverse drain current (pulsed) | | (Note 1) | I _{DRP} | 56 | |
| Channel temperature | | | T _{ch} | 150 | °C |
| Storage temperature | | | T _{stg} | -55 to 150 | |
| Isolation voltage (RMS) | (t = 1.0 s) | | V _{ISO(RMS)} | 2000 | V |
| Mounting torque | | | TOR | 0.6 | N · m |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production

2025-09

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5. Thermal Characteristics

| Characteristics | | Max | Unit |
|---------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | | 3.12 | °C/W |
| Channel-to-ambient thermal resistance | R _{th(ch-a)} | 62.5 | |

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2: V_{DD} = 90 V, T_{ch} = 25 °C (initial), L = 20.7 mH, I_{AS} = 3.3 A

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

6.1. Static Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------------------|---|-----|-------|------|------|
| Gate leakage current | I _{GSS} | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$ | _ | _ | ±1 | μΑ |
| Drain cut-off current | I _{DSS} | V _{DS} = 600 V, V _{GS} = 0 V | | | 2 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = 10 mA, V _{GS} = 0 V | 600 | _ | | ٧ |
| Gate threshold voltage | V_{th} | $V_{DS} = 10 \text{ V}, I_D = 0.48 \text{ mA}$ | 3 | | 4 | |
| Drain-source on-resistance | R _{DS(ON)} | V_{GS} = 10 V, I_D = 4.2 A | _ | 0.158 | 0.19 | Ω |

6.2. Dynamic Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------|--------------------|---|-----|------|-----|------|
| Input capacitance | | C _{iss} | $V_{DS} = 300 \text{ V}, V_{GS} = 0 \text{ V}, f = 100 \text{ kHz}$ | _ | 1060 | _ | pF |
| Reverse transfer capacitance | | C _{rss} | | _ | 1.7 | | |
| Output capacitance | | C _{oss} | | _ | 30 | _ | |
| Effective output capacitance (energy related) | (Note 3) | C _{o(er)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 50 | | |
| Effective output capacitance (time related) | (Note 4) | C _{o(tr)} | V _{DS} = 0 to 400 V, V _{GS} = 0 V | _ | 330 | | |
| Gate resistance | | r _g | V _{DS} = OPEN , f = 1 MHz | _ | 2.8 | _ | Ω |
| Switching time (rise time) | | t _r | See Fig. 6.2.1 | _ | 18 | _ | ns |
| Switching time (turn-on time) | | t _{on} | | _ | 36 | _ | |
| Switching time (fall time) | | t _f | | _ | 5 | _ | |
| Switching time (turn-off time) | | t _{off} | | _ | 55 | _ | |
| MOSFET dv/dt ruggedness | | dv/dt | $V_{DS} \le V_{DSS}$, $I_D \le 10 \text{ A}$ | 70 | _ | _ | V/ns |

Note 3: $C_{O(er)}$ is a fixed capacitance that gives the same stored energy as C_{OSS} while V_{DS} is rising from 0 V to 400 V. Note 4: $C_{O(tr)}$ is a fixed capacitance that gives the same charging time as C_{OSS} while V_{DS} is rising from 0 V to 400 V.

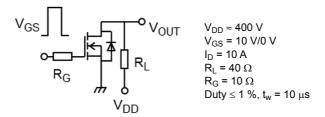


Fig. 6.2.1 Switching Time Test Circuit



6.3. Gate Charge Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|------------------|---|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 14 \text{ A}$ | _ | 20 | | nC |
| Gate-source charge 1 | Q _{gs1} | | | 6 | | |
| Gate-drain charge | Q_{gd} | | _ | 6 | | |

6.4. Source-Drain Characteristics (T_a = 25 °C unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|-------------------------------|-----------------|--|-----|------|------|------|
| Diode forward voltage | V_{DSF} | I _{DR} = 14 A, V _{GS} = 0 V | _ | _ | -1.7 | V |
| Reverse recovery time | | V _{DD} = 400 V, | _ | 240 | _ | ns |
| Reverse recovery charge | Q_{rr} | I _{DR} = 7 A, V _{GS} = 0 V -dI _{DR} /dt = 100 A/μs | _ | 2.3 | _ | μС |
| Peak reverse recovery current | I _{rr} | -αι _{DR} /αι – 100 Α/μδ | _ | 19 | _ | Α |
| Diode dv/dt ruggedness | dv/dt | $V_{DD} \le 400 \text{ V}, I_{DR} \le 7 \text{ A}, V_{GS} = 0 \text{ V}$ | 25 | _ | _ | V/ns |

7. Marking (Note)

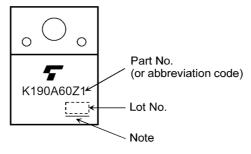


Fig. 7.1 Marking

Note: A line under a Lot No. identifies the indication of product Labels.

Not underlined: [[Pb]]/INCLUDES > MCV

Underlined: [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.



8. Characteristics Curves (Note)

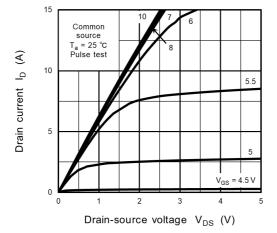


Fig. 8.1 I_D - V_{DS}

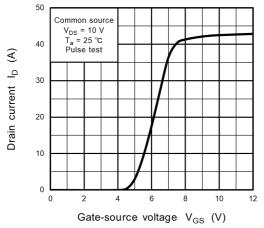


Fig. 8.3 I_D - V_{GS}

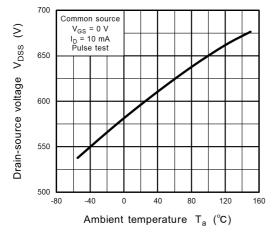


Fig. 8.5 V_{DSS} - T_a

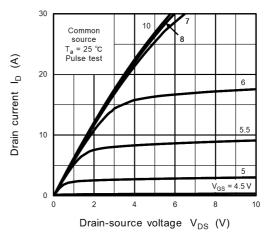


Fig. 8.2 I_D - V_{DS}

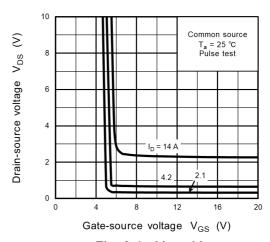


Fig. 8.4 V_{DS} - V_{GS}

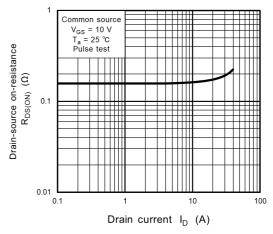
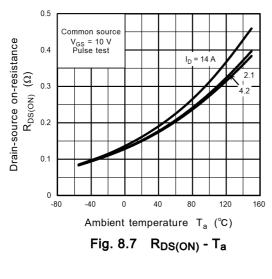
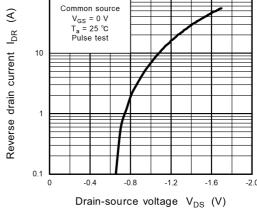


Fig. 8.6 R_{DS(ON)} - I_D

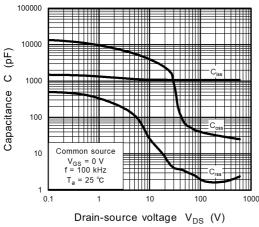






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Fig. 8.8 I_{DR} - V_{DS}



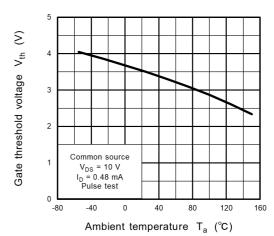
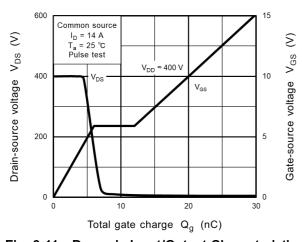


Fig. 8.9 C - V_{DS}

Fig. 8.10 V_{th} - T_a



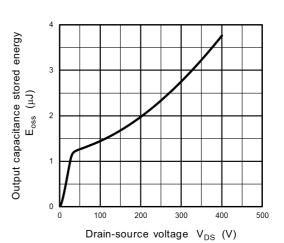


Fig. 8.11 Dynamic Input/Output Characteristics

Fig. 8.12 E_{OSS} - V_{DS}



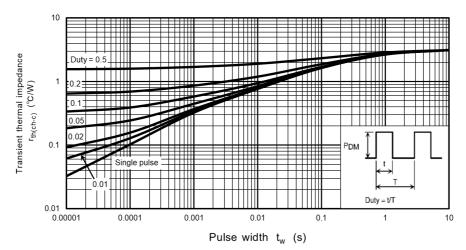


Fig. 8.13 r_{th} - t_w (Guaranteed Maximum)

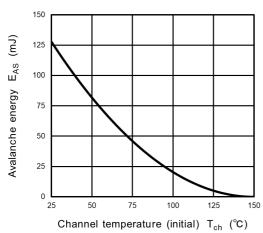
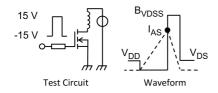


Fig. 8.14 E_{AS} - T_{ch} (Guaranteed Maximum)



$$V_{DD} = 90 \text{ V, L} = 20.7 \text{ mH}$$
 $E_{AS} = \frac{1}{2} \cdot \text{L} \cdot \text{I}_{AS}^2 \cdot \left(\frac{\text{B}_{VDSS}}{\text{B}_{VDSS} - \text{V}_{DD}} \right)$

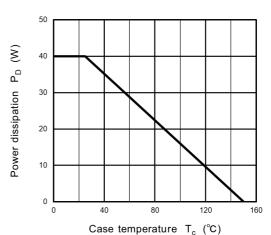


Fig. 8.15 P_D - T_c (Guaranteed Maximum)

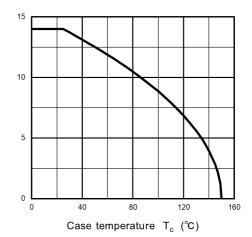


Fig. 8.17 I_D - T_c (Guaranteed Maximum)

Fig. 8.16 Test Circuit/Waveform

Drain current I_D (A)



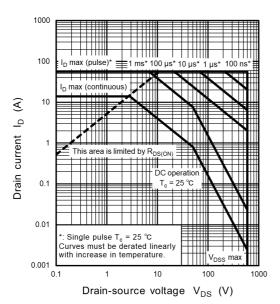


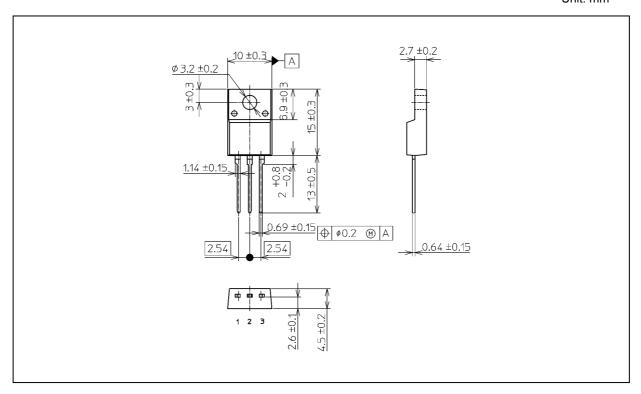
Fig. 8.18 Safe Operating Area (Guaranteed Maximum)

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



Package Dimensions

Unit: mm



Weight: 1.7 g (typ.)

| Package Name(s) | |
|---------------------|---|
| TOSHIBA: 2-10U1S | |
| Nickname: TO-220SIS | ٦ |



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